NSN 5961-01-230-9777

Semiconductor Device Set - Page 1 of 2

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Inclosure Material:

Glass all semiconductor device diode

Overall Length:

0.300 inches all semiconductor device diode

Terminal Length:

1.000 inches all semiconductor device diode

Overall Diameter:

0.107 inches all transistor

Internal Configuration:

Junction contact all semiconductor device diode

Internal Junction Configuration:

Pn all semiconductor device diode

Component Function Relationship:

Matched

Component Name And Quantity:

4 semiconductor device diode

Mounting Method:

Terminal all semiconductor device diode

Features Provided:

Hermetically sealed case and quality assurance level tx

Semiconductor Material:

Silicon all semiconductor device diode

Voltage Rating In Volts Per Characteristic:

50.0 reverse voltage, instantaneous all semiconductor device diode

Current Rating Per Characteristic:

115.00 milliamperes forward current, average blank all semiconductor device diode

Power Rating Per Characteristic:

250.0 milliwatts small-signal input power, common-collector of standard range all semiconductor device diode

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air all semiconductor device diode

Precious Material And Location:

Terminal surfaces option gold

Precious Material:

Gold

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead all semiconductor device diode

Specification Data:

81349-mil-s-19500/284 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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